

**DYNAMIC CHARACTERISTICS**

**APT6040BVR**

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$		2600	3120	pF
$C_{oss}$	Output Capacitance			305	425	
$C_{rss}$	Reverse Transfer Capacitance			125	180	
$Q_g$	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 300V$ $I_D = 16A @ 25^\circ C$		115	170	nC
$Q_{gs}$	Gate-Source Charge			15	25	
$Q_{gd}$	Gate-Drain ("Miller") Charge			52	75	
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 300V$ $I_D = 16A @ 25^\circ C$ $R_G = 1.6\Omega$		10	20	ns
$t_r$	Rise Time			9	18	
$t_{d(off)}$	Turn-off Delay Time			38	50	
$t_f$	Fall Time			6	12	

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS**

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$I_S$	Continuous Source Current (Body Diode)			16	Amps
$I_{SM}$	Pulsed Source Current ① (Body Diode)			64	
$V_{SD}$	Diode Forward Voltage ② ( $V_{GS} = 0V, I_S = -15A$ )			1.3	Volts
$t_{rr}$	Reverse Recovery Time ( $I_S = -15A, di_S/dt = 100A/\mu s$ )		400		ns
$Q_{rr}$	Reverse Recovery Charge ( $I_S = -15A, di_S/dt = 100A/\mu s$ )		6		$\mu C$

**THERMAL CHARACTERISTICS**

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.50	$^\circ C/W$
$R_{\theta JA}$	Junction to Ambient			40	

① Repetitive Rating: Pulse width limited by maximum junction temperature.

③ See MIL-STD-750 Method 3471

② Pulse Test: Pulse width < 380  $\mu s$ , Duty Cycle < 2%

④ Starting  $T_j = +25^\circ C$ ,  $L = 7.50mH$ ,  $R_G = 25\Omega$ , Peak  $I_L = 16A$

APT Reserves the right to change, without notice, the specifications and information contained herein.

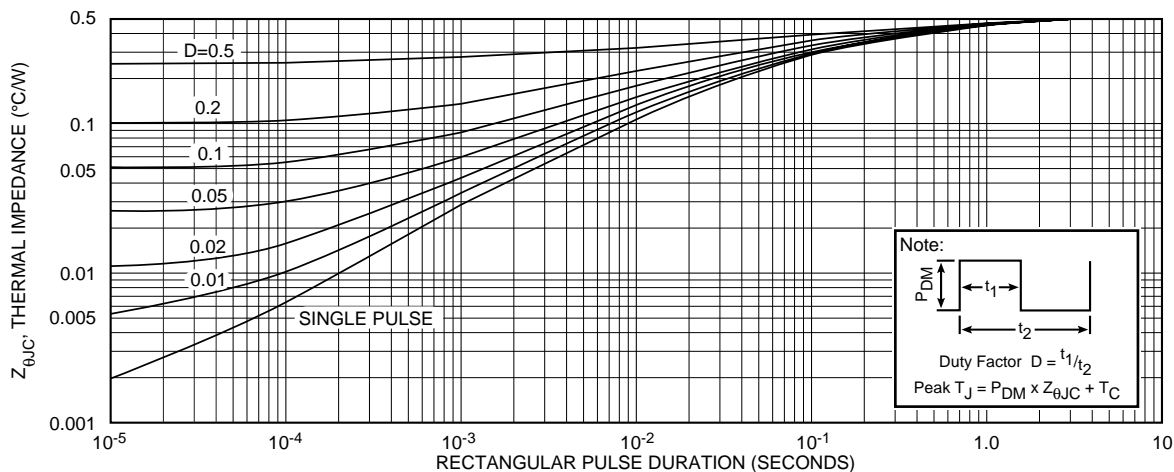


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

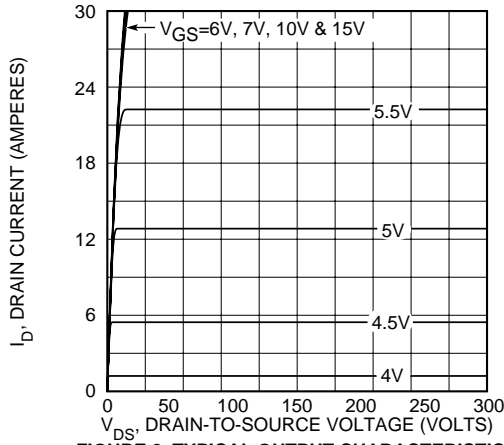


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

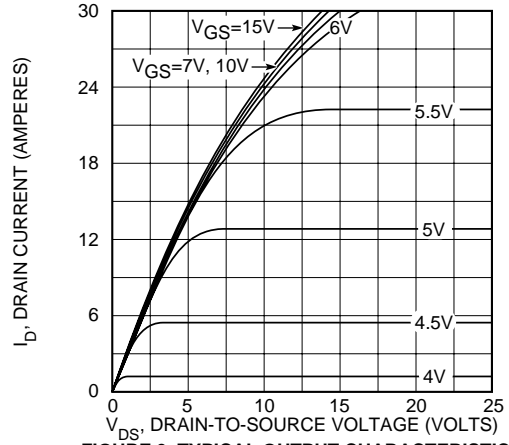


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

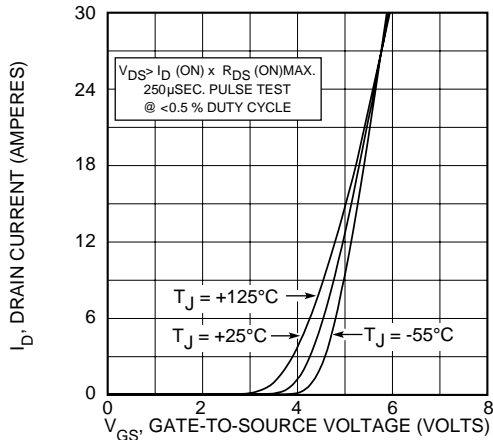


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

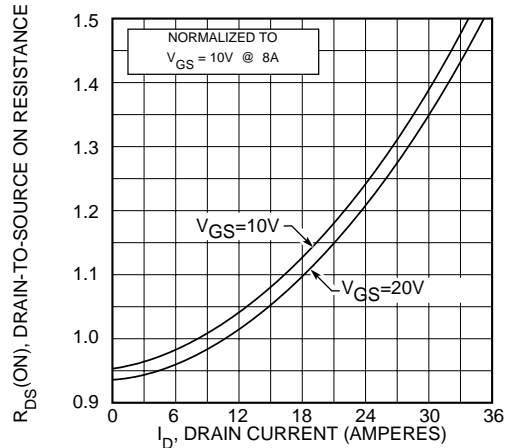


FIGURE 5,  $R_{DS(ON)}$  vs DRAIN CURRENT

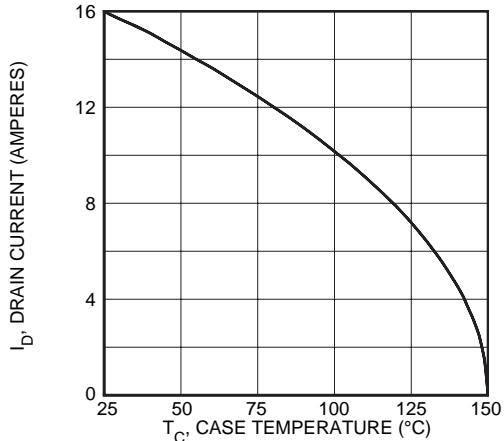


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

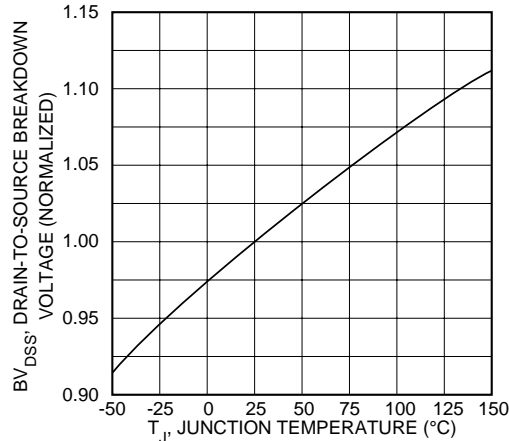


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

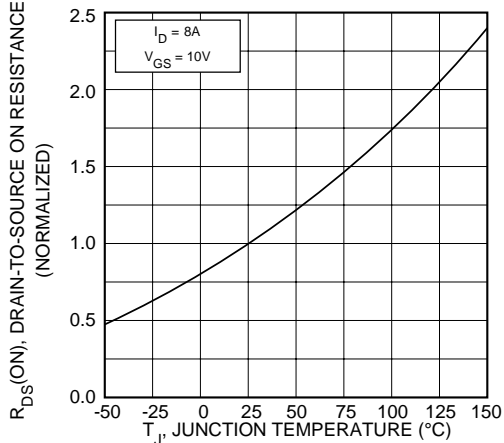


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

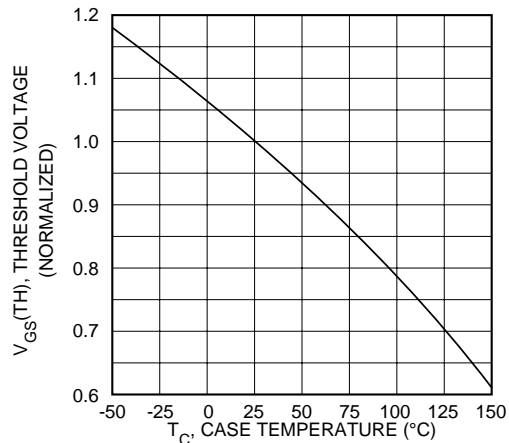


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

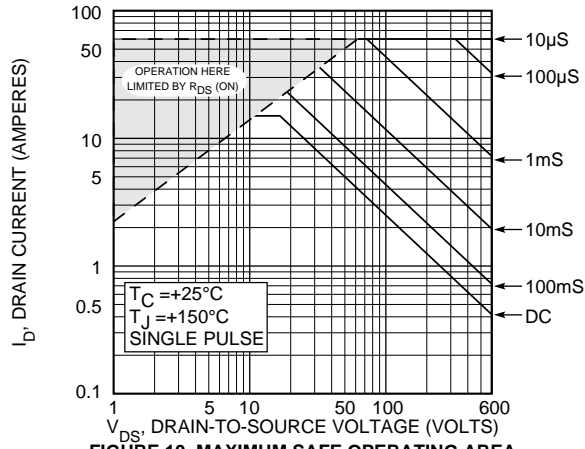


FIGURE 10, MAXIMUM SAFE OPERATING AREA

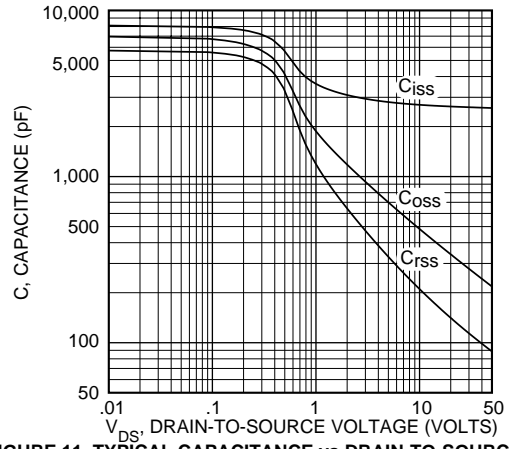


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

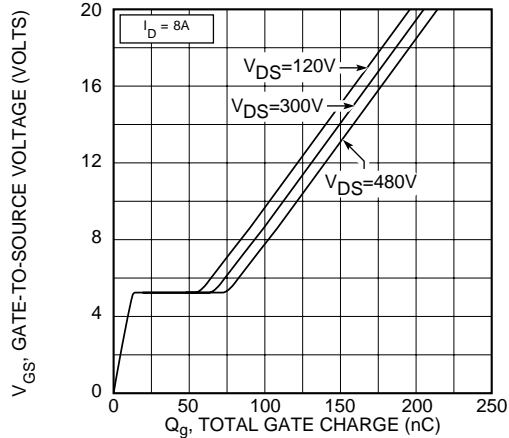


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

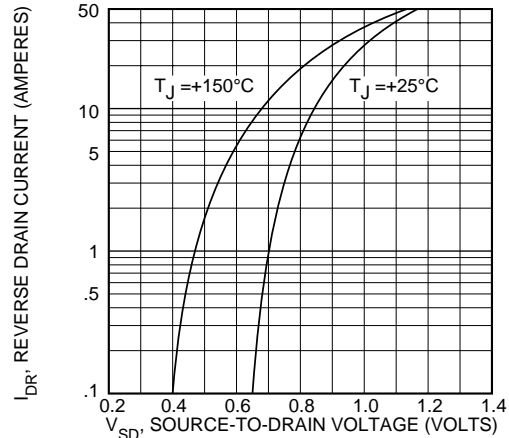
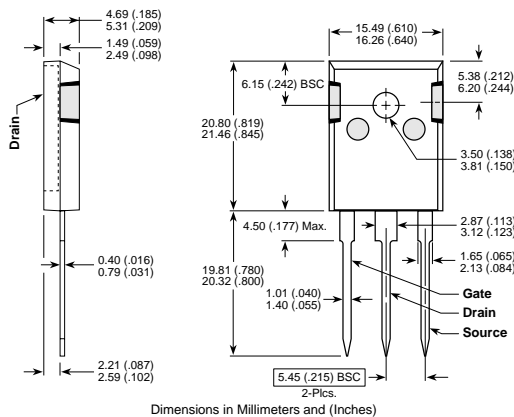


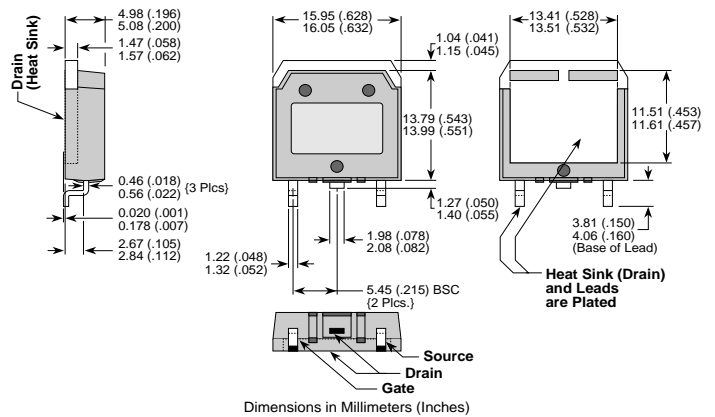
FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

TO-247 Package Outline



Dimensions in Millimeters and (Inches)

D<sup>3</sup>PAK Package Outline



Dimensions in Millimeters (Inches)

APT's devices are covered by one or more of the following U.S. patents: 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336  
5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058